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Editors

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Contents

vii *Authors*
ix *Conference Committee*

GROWTH I: BULK GROWTH AND EPITAXY

11280 02 **Recent progress of large size and low dislocation bulk GaN growth (Invited Paper)** [11280-1]

GROWTH II: CHARACTERIZATION AND DISLOCATIONS

11280 09 **Dislocation density reduction in $(10\bar{1}\bar{1})$ GaN at a high temperature using tri-halide vapor phase epitaxy** [11280-8]

MATERIAL CHARACTERIZATION: POINT DEFECTS

11280 0B **Origin and dynamic properties of major intrinsic nonradiative recombination centers in wide bandgap nitride semiconductors (Invited Paper)** [11280-10]

11280 0C **Control of vacancy-type defects in Mg implanted GaN studied by positron annihilation spectroscopy (Invited Paper)** [11280-11]

11280 0E **Degradation and recovery of high-periodicity InGaN/GaN MQWs under optical stress in short-circuit condition** [11280-13]

VCSEL AND RCLED

11280 0H **Blue semipolar III-nitride vertical-cavity surface-emitting lasers (Invited Paper)** [11280-15]

11280 0I **Nonpolar GaN-based VCSELs with lattice-matched nanoporous distributed Bragg reflector mirrors (Invited Paper)** [11280-16]

11280 0M **GaN-based vertical-cavity surface-emitting laser incorporating a TiO₂ high-index-contrast grating** [11280-20]

LED: LIGHT EXTRACTION AND EFFICIENCY

11280 0O **PECVD grown SiN photonic crystal micro-domes for the light extraction enhancement of GaN LEDs** [11280-22]

IN-PLANE LASER DIODES AND NONLINEAR OPTICS

- 11280 OS **Blue and green InGaN semiconductor lasers as light sources for displays** [11280-26]
- 11280 OT **Angular resolved far-field dynamics of (Al,In)GaN laser diodes** [11280-27]

IN-PLANE LASER DIODES: VISIBLE AND UV

- 11280 OY **Critical discussion of the determination of internal losses in state-of-the-art (Al,In)GaN laser diodes** [11280-32]
- 11280 OZ **Degradation mechanisms of 1.6 W blue semiconductor lasers: effect on subthreshold optical power and power spectral density** [11280-33]
- 11280 10 **Monolithically p-down nitride laser diodes and LEDs obtained by MBE using buried tunnel junction design** [11280-34]

UV LED

- 11280 15 **Role of defects in the mid-term degradation of UV-B LEDs investigated by optical and DLTS measurements** [11280-39]
- 11280 18 **Enhancement of light extraction efficiency of 280-nm deep-UV LEDs using SiO₂ microsphere and microlens arrays** [11280-42]

MICROLED AND NANOSTRUCTURED DEVICES I

- 11280 1C **Analysis of InGaN surfaces after chemical treatments and atomic layer deposition of Al₂O₃ for μ LED applications** [11280-46]

MICROLED AND NANOSTRUCTURED DEVICES II

- 11280 1E **Application of porous GaN for microLED (Invited Paper)** [11280-48]
- 11280 1F **The photonic properties of micro/mini LED arrays with different substrate thickness (Invited Paper)** [11280-49]

ELECTRONIC DEVICES

- 11280 11 **Out-diffusion of Pd as a potential degradation mechanism in GaN HEMTs with Ni-Pd-Au Schottky contacts** [11280-52]

Authors

Numbers in the index correspond to the last two digits of the seven-digit citation identifier (CID) article numbering system used in Proceedings of SPIE. The first five digits reflect the volume number. Base 36 numbering is employed for the last two digits and indicates the order of articles within the volume. Numbers start with 00, 01, 02, 03, 04, 05, 06, 07, 08, 09, 0A, 0B...0Z, followed by 10-1Z, 20-2Z, etc.

Altuntaş, İ., 0O
Amano, H., 15
Aragon, Andrew A., 0I
Avrutin, V., 0O
Aydinli, A., 0O
Back, Joonho, 0H
Banayeem, Hassan, 0T
Bengtsson, Jörgen, 0M
Bharadwaj, Shyam, 10
Brodie, Miles, 1I
Bruederl, Georg, 0T
Buffolo, M., 0Z
Cadot, Stéphane, 1C
Caria, Alessandro, 0E
Chang, Feng-Pin, 1F
Chang, Tsu-Chi, 0M
Chao, Chia-Hsin, 1F
Chen, Chen, 1E
Chen, Hong, 0E
Chen, Yu-Sheng, 1F
Chichibu, Shigefusa F., 0B, 0C
Chlipala, Mikolaj, 10
Choi, Joo Won, 1E
Chu, Chun-Wen, 1F
Cohen, Daniel A., 0H
Damm, Matthias, 0T
Deki, M., 15
Demir, İ., 0O
DenBaars, Steven P., 0H
De Santi, Carlo, 0E, 0Z, 15
Dickmann, Marcel, 0C
Egger, Werner, 0C
Elagöz, S., 0O
Enatsu, Yuuki, 02
Fang, Yen-Hsiang, 1F
Feezell, Daniel F., 0I
Fu, Houqiang, 0E
Genç, M., 0O
Gheeraert, Etienne, 1C
Gülseren, O., 0O
Gür, E., 0O
Gustavsson, Johan, 0M
Haglund, Åsa, 0M
Hajdel, Mateusz, 10
Hara, Yoshihiro, 0S
Hashemi, Ehsan, 0M
Hirao, Tsuyoshi, 0S
Huang, Xuanqi, 0E
Hubbard, William, 1I
Hugenschmidt, Christoph, 0C
Ikeda, Hirotaka, 02
Ishibashi, Shoji, 0B, 0C
Ishinabe, Takayuki, 02
Iso, Kenji, 02, 09
Izumisawa, Satoru, 02
Jena, Debdeep, 10
Kagamitani, Yuji, 02
Kearns, Jared A., 0H
Kido, Yuka, 09
Kohlstedt, Raphael, 0Y
Kojima, Kazunobu, 0B
König, Harald, 0T
Koukitu, Akinori, 09
Kubota, Kohei, 02
Kunzmann, Dominic J., 0Y
Kushimoto, M., 15
Le Maoult, Corentin, 1C
Lee, SeungGeun, 0H
Lin, Chien-Chung, 1F
Lingley, Zachary, 1I
Liu, Cheng, 18
Lu, Tien-Chang, 0M
Luk, Ting S., 0I
Martin, François, 1C
Martinez, Eugénie, 1C
Masui, Shingo, 0S
Melanson, Bryan, 18
Meneghesso, Gaudenzio, 0E, 0Z, 15
Meneghini, Matteo, 0E, 0Z, 15
Mikawa, Yutaka, 02
Mishkat-Ul-Masabih, Saadat M., 0I
Miyata, Erina, 09
Mochizuki, Tae, 02
Monavarian, Morteza, 0I
Morkoç, H., 0O
Mu, Yijie, 0T
Murakami, Hisashi, 09
Muziol, Grzegorz, 10
Nagahama, Shin-ichi, 0S
Nagao, Yoji, 0S
Nakamura, Shuji, 0H
Nakatsu, Yoshitaka, 0S
Nolot, Emmanuel, 1C
Nowakowski-Szkudlarek, Krzesimir, 10
Ohtaki, Shoma, 09
Özgür, Ü., 0O
Palmquist, Nathan C., 0H
Piva, F., 0Z, 15

Schwarz, Ulrich T., OT, OY
Sheremet, V., OO
Shibata, N., 15
Shima, Kohei, OB
Siekacz, Marcin, 10
Sin, Yongkun, 11
Sitzman, Scott, 11
Skierbiszewski, Czeslaw, 10
Song, Jie, 1E
Stanczyk, Szymon, 10
Taffarel, M., OZ
Takahashi, Tatsuya, O2
Tautz, Soenke, OT
Tomozawa, H., 15
Tsukada, Yusuke, O2
Turski, Henryk, 10
Uedono, Akira, OB, OC
Uhlig, Tino, OY
Vaufrey, David, 1C
Veksler, Dmitry, 11
Wang, Kai, 1E
Wang, Po-Hsun, 1F
Wu, Chih-I, 1F
Wu, Dan, 1E
Xing, Huili, 10
Yanamoto, Tomoya, OS
Yang, Shu-Mei, 1F
Zak, Mikolaj, 10
Zamperetti, Filippo, OE
Zanoni, Enrico, OE, OZ, 15
Zhang, Jing, 18
Zhao, Yuji, OE

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- 1 Growth I: Bulk Growth and Epitaxy
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- 2 Growth II: Characterization and Dislocations
Shigefusa F. Chichibu, Tohoku University (Japan)
- 3 Material Characterization: Point Defects
Michal Bockowski, Institute of High Pressure Physics (Poland)
- 4 VCSEL and RCLED
Piotr Perlin, Institute of High Pressure Physics (Poland)
- 5 LED: Light Extraction and Efficiency
Daniel F. Feezell, The University of New Mexico (United States)
- 6 In-Plane Laser Diodes and Nonlinear Optics
Åsa Haglund, Chalmers University of Technology (Sweden)
- 7 In-Plane Laser Diodes: Visible and UV
Lucja Marona, Institute of High Pressure Physics (Poland)
- 8 UV LED
Andreas Waag, Technische Universität Braunschweig (Germany)

- 9 MicroLED and Nanostructured Devices I
Martin D. Dawson, Fraunhofer UK Research Ltd. (United Kingdom)
- 10 MicroLED and Nanostructured Devices II
Zlatko Sitar, North Carolina State University (United States)
- 11 Electronic Devices
Hiroshi Fujioka, Institute of Industrial Science, The University of Tokyo
(Japan)

